

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior revisions, and listings, of claims in the application.

Listing of Claims:

1. (*Currently Amended*) A III-nitride compound semiconductor light-emitting device comprising:
having

a plurality of III-nitride compound semiconductor layers that are epitaxially grown using a substrate, wherein the plurality of III-nitride compound semiconductor layers including:
includes

an active layer generating light by recombination of electrons and holes and containing gallium and nitrogen,

an n-type $\text{Al}(x)\text{In}(y)\text{Ga}(1-x-y)\text{N}$ layer epitaxially grown before the active layer is grown, and

an n-type electrode electrically contacting with the n-type $\text{Al}(x)\text{In}(y)\text{Ga}(1-x-y)\text{N}$ layer, and

wherein the n-type $\text{Al}(x)\text{In}(y)\text{Ga}(1-x-y)\text{N}$ layer has a top surface which is exposed by etching, the exposed top surface includes a region for scribing and breaking the device and a region for contact with the n-type electrode, and ~~the surface of the region for scribing and breaking the device is roughened, the~~ a top surface of the region for scribing and breaking the device including a roughened surface such that having rough surface through which light generated from the active layer escapes outwardly from the device through said roughened surface.

2. (*Currently Amended*) The III-nitride compound semiconductor light-emitting device of claim 1, wherein the roughened top surface of the region for scribing and breaking the device is formed by dry etching.

3. (*Original*) The III-nitride compound semiconductor light-emitting device of claim 2, wherein a mask pattern is used in the dry etching.

4. (*Original*) The III-nitride compound semiconductor light-emitting device of claim 3, wherein surface gratings are formed by means of the mask pattern, the surface area of each of the surface gratings is in a range of $1.5\ \mu\text{m}^2$ to $4\ \mu\text{m}^2$.

5. (*Original*) The III-nitride compound semiconductor light-emitting device of claim 3, wherein surface gratings are formed by means of the mask pattern, the height of each of the surface gratings is in a range of $0.5\ \mu\text{m}$ to $1.5\ \mu\text{m}$.

6. (*Original*) The III-nitride compound semiconductor light-emitting device of claim 3, wherein etching residues are used as the mask pattern in the dry etching.

7. (*Original*) The III-nitride compound semiconductor light-emitting device of claim 6, wherein protrusions are formed by mean of the mask pattern and each of the protrusions has a conical shape.

8. *(Original)* The III-nitride compound semiconductor light-emitting device of claim 7, wherein the diameter of the bottom of the conical shape is in the range of 1 nm to 10 μm .

9. *(Original)* The III-nitride compound semiconductor light-emitting device of claim 7, wherein the height of the conical shape is in the range of 1 nm to 10 μm .

10. *(Currently Amended)* The III-nitride compound semiconductor light-emitting device of claim 1, wherein the roughened top surface of the region for scribing and breaking the device is formed by wet etching.

11. *(Original)* The III-nitride compound semiconductor light-emitting device of claim 10, wherein the wet etching is a photoelectrochemical etching.

12. *(Original)* The III-nitride compound semiconductor light-emitting device of claim 11, wherein KOH solution is used as an etching solution in the photoelectrochemical etching.

13. *(Original)* The III-nitride compound semiconductor light-emitting device of claim 3, wherein the dry etching is performed after the region for contact with the n-type electrode is etched.